



Silicon Standard Recovery Diode

Features

- High Surge Capability
- Types up to 600 V V_{RRM}

DO-5 Package



Maximum ratings, at $T_J = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	1N3208 (R)	1N3209 (R)	1N3210 (R)	1N3211 (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		50	100	200	300	V
RMS reverse voltage	V_{RMS}		35	70	140	210	V
DC blocking voltage	V_{DC}		50	100	200	300	V
Continuous forward current	I_F	$T_C \leq 150\text{ }^\circ\text{C}$	15	15	15	15	A
Surge non-repetitive forward current, Half Sine Wave	I_{FSM}	$T_C = 25\text{ }^\circ\text{C}$, $t_p = 8.3\text{ ms}$	297	297	297	297	A
Operating temperature	T_J		-65 to 175	-65 to 175	-65 to 175	-65 to 175	$^\circ\text{C}$
Storage temperature	T_{stg}		-65 to 175	-65 to 175	-65 to 175	-65 to 175	$^\circ\text{C}$

Electrical characteristics, at $T_J = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	1N3208 (R)	1N3209 (R)	1N3210 (R)	1N3211 (R)	Unit
Diode forward voltage	V_F	$I_F = 15\text{ A}$, $T_J = 25\text{ }^\circ\text{C}$	1.5	1.5	1.5	1.5	V
Reverse current	I_R	$V_R = 50\text{ V}$, $T_J = 25\text{ }^\circ\text{C}$	10	10	10	10	μA
		$V_R = 50\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$	10	10	10	10	mA
Thermal characteristics							
Thermal resistance, junction - case	$R_{\theta JC}$		0.65	0.65	0.65	0.65	$^\circ\text{C/W}$



Figure 1-Typical Forward Characteristics

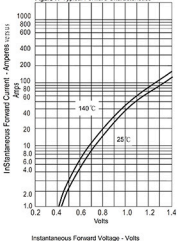
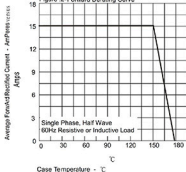


Figure 2-Forward Derating Curve



Peak Forward Surge Current - Amperes versus

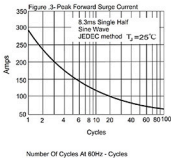


Figure 4-Typical Reverse Characteristics

